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Data Sheet

LED Chip Infrared

EOLC-760-17

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Radiation	Type	Electrodes
Infrared	AlGaAs, DDH	P (anode) up

<p>All dimensions in microns Chip dimensions: $\pm 25 \mu\text{m}$ Metallization pad dimensions: $\pm 15 \mu\text{m}$</p>	<p>Electrodes: gold alloy Wire bond contact can also have a square shape</p>
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Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.65	1.95	V
Reverse current	$V_R = 5 \text{ V}$	I_R			10	μA
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e	4	5		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	750	760	770	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		29		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		25; 16		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 131 142



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.